

isc Silicon NPN Power Transistor

2SC3994

DESCRIPTION

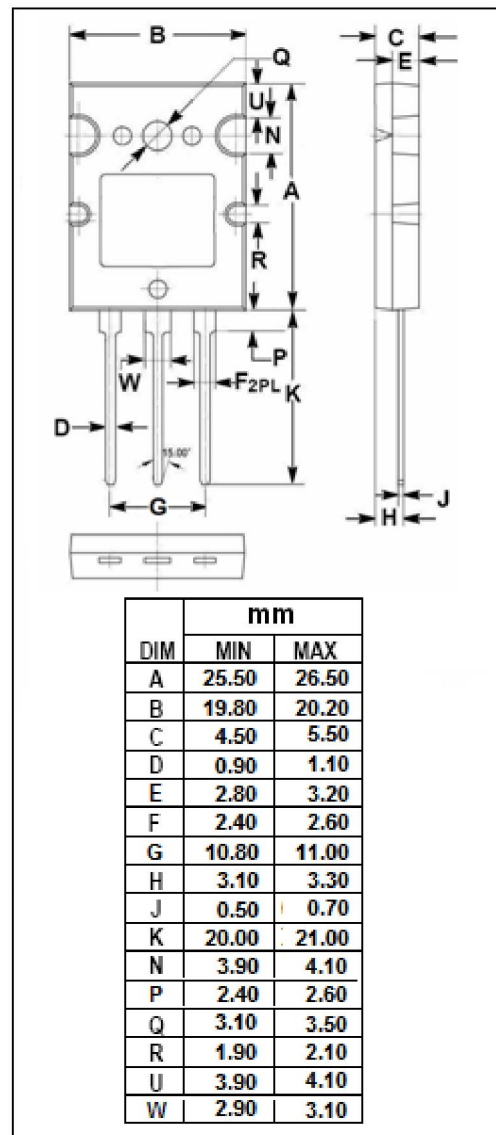
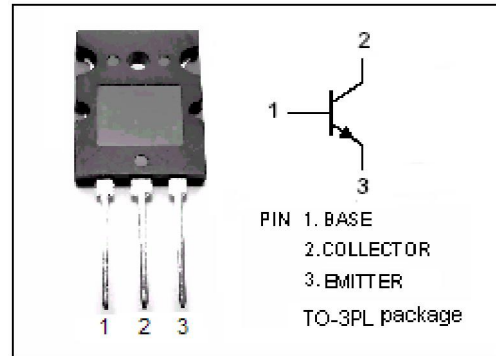
- High Switching Speed
- High Breakdown Voltage-
: $V_{(BR)CBO} = 1100V(\text{Min})$

APPLICATIONS

- Designed for horizontal deflection output applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1100	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	25	A
I_{CM}	Collector Current-Pulse	60	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}\text{C}$	300	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}\text{C}$



isc Silicon NPN Power Transistor**2SC3994****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=10\text{mA}; I_B=0$	800			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=12\text{A}; I_B=2.4\text{A}$			2.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=12\text{A}; I_B=2.4\text{A}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=800\text{V}; I_E=0$			10	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			10	μA
h_{FE-1}	DC Current Gain	$I_C=1.6\text{A}; V_{CE}=5\text{V}$	10		60	
h_{FE-2}	DC Current Gain	$I_C=8\text{A}; V_{CE}=5\text{V}$	8			
t_{stg}	Storage Time	$V_{CC}=400\text{V}, 5I_{B1}=-2.5I_{B2}=I_C=20\text{A}, R_L=20\Omega$			3.0	μs
t_f	Fall Time				0.3	μs